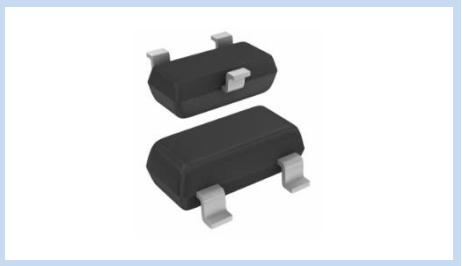
N-Channel MOSFET
60V 0.3A SOT-23 ESD AEC-Q101

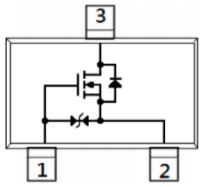
MFT6NA30S23EA

MERITEK

FEATURE



- $R_{DS(ON)}$<3Ω, V_{GS}=10V, I_D=500mA
- $R_{DS(ON)}$<4Ω, V_{GS}=4.5V, I_D= 200mA
- Advanced Trench Process Technology
- High Density Cell Design For Ultra Low On-Resistance
- Application: Battery Operated Systems, Solid-State Relays, Displays, Lamps, Solenoids, Memories, etc
- ESD Protected 2KV HBM
- AEC-Q101 Qualified



RoHS

MECHANICAL DATA

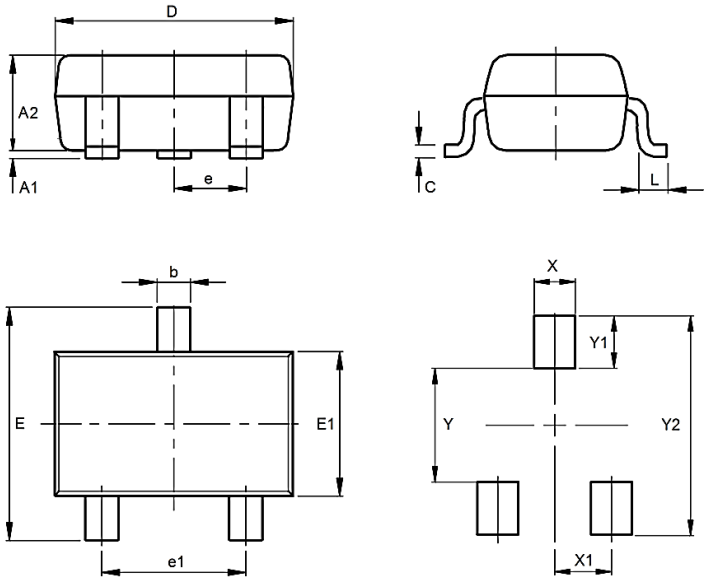
- Case: SOT-23 Package
- Terminals: Solderable per MIL-STD-750, Method 2026

MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Drain Current – Continuous		I_D	300	mA
Drain Current – Pulsed		I_{DM}	2000	mA
Power Dissipation	T_A=25°C	P_D	500	mW
	Derate above 25°C		4	mW/°C°
Operating Junction Temperature and Storage Temperature		T_J, T_{stg}	-55 to 150	°C
Thermal Resistance, Junction to Ambient		$R_{\theta JA}$	250	°C / W

DIMENSIONS

Item	Min (mm)	Max (mm)
A1	0.00	0.10
A2	0.90	1.10
b	0.35	0.50
C	0.08	0.20
D	2.80	3.04
e	0.90	1.00
e1	1.80	2.00
E	2.20	2.60
E1	1.20	1.40
L	0.15	
X	0.80	
X1	0.95	
Y	1.10	
Y1	0.90	
Y2	2.90	

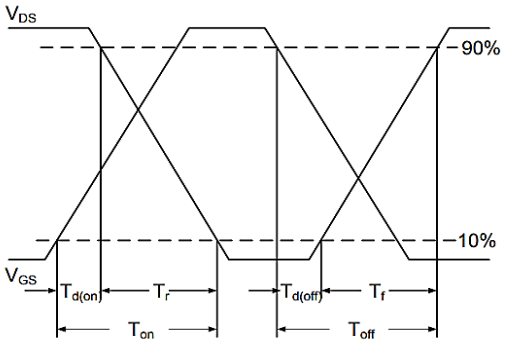


ELECTRICAL CHARACTERISTICS

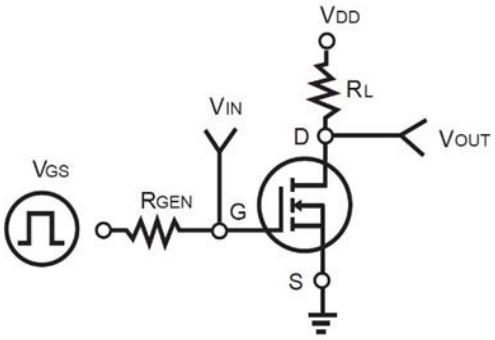
Off Characteristics	Conditions	Symbol	Min	Typ.	Max	Unit
Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=10μA	BV_{DSS}	60	--	--	V
Gate Threshold Voltage	V_{GS}=V_{DS}, I_D=250μA	$V_{GS(th)}$	1.0	--	2.5	V
Gate Leakage Current	V_{DS}=0V, V_{GS}=±20V	I_{GSS}	--	--	±10	μA
Zero Gate Voltage Drain Current	V_{DS}=60V, V_{GS}=0V	I_{DSS}	--	--	1	μA
On Characteristics	**Conditions**	**Symbol**	**Min**	**Typ.**	**Max**	**Unit**
Static Drain-Source On-Resistance	V_{GS}=10V, I_D=500mA	$R_{DS(ON)}$	--	--	3	Ω
	V_{GS}=4.5V, I_D=200mA		--	--	4	
Dynamic Characteristics	**Conditions**	**Symbol**	**--**	**Typ.**	**Max**	**Unit**
Input Capacitance	V_{DS}=25V, V_{GS}=0V f=1.0MHz	C_{iss}	--	35	--	pF
Output Capacitance		C_{oss}	--	13	--	
Reverse Transfer Capacitance		C_{rss}	--	8	--	
Turn-On Delay Time	V_{DS}=30V, I_D=200mA, V_{GS}=10V, R_G=10Ω	$T_{d(on)}$	--	2.7	--	nS
Rise Time		T_r	--	19	--	
Turn-Off Delay Time		$T_{d(off)}$	--	15	--	
Fall Time		T_f	--	23	--	
Total Gate Charge	V_{DS}= 5V, V_{GS}=5V, I_D=250mA	Q_g	--	0.8	--	nC
Gate-Source Charge		Q_{gs}	--	0.35	--	
Gate-Drain Charge		Q_{gd}	--	0.2	--	
Drain-Source Body Diode	**Conditions**	**Symbol**	**Min**	**Typ.**	**Max**	**Unit**
Diode Forward Voltage	I_S=200mA,V_{GS}=0V	V_{SD}	--	0.82	1.3	V
Forward Transconductance	V_{DS}=15V, I_D=250mA	g_{FS}	100	--	--	mS
Diode Foward Current	---	I_S	--	--	300	mA

Note:
1. T_A = 25°C Exposure to absolute maximum rating conditions for extended periods may remain possibility to affect device reliability
2. Pulse width<300μs, Duty cycle<2%.
3. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz square pad of copper.
4. Guaranteed by design, not subject to production testing.
5. The maximum current rating is package limited.

Switching Time Waveform

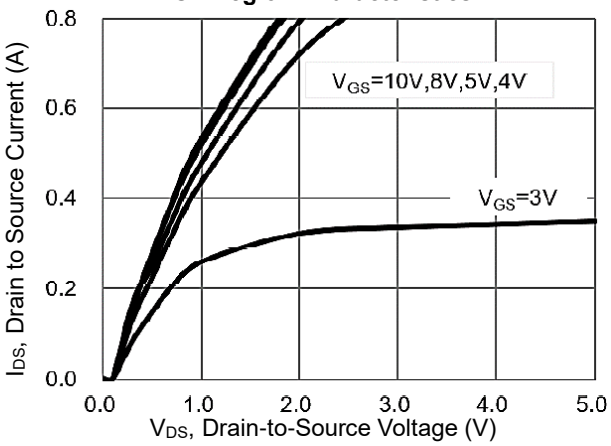


Switching Test Circuit

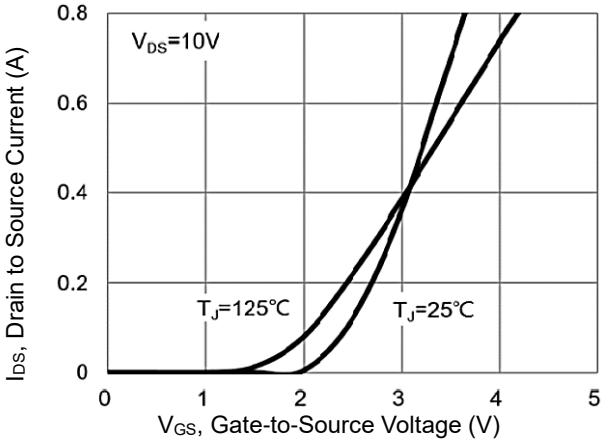


CHARACTERISTIC CURVES

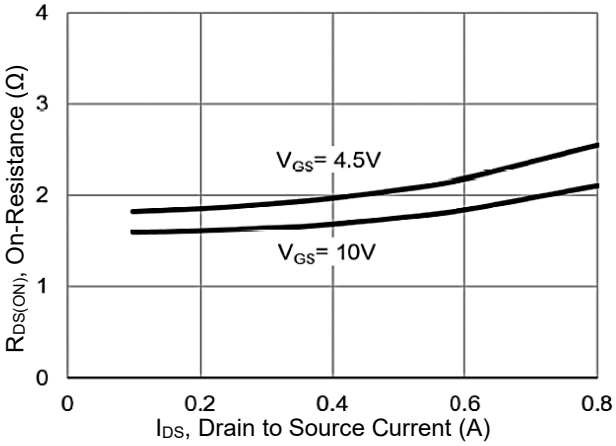
On Region Characteristics



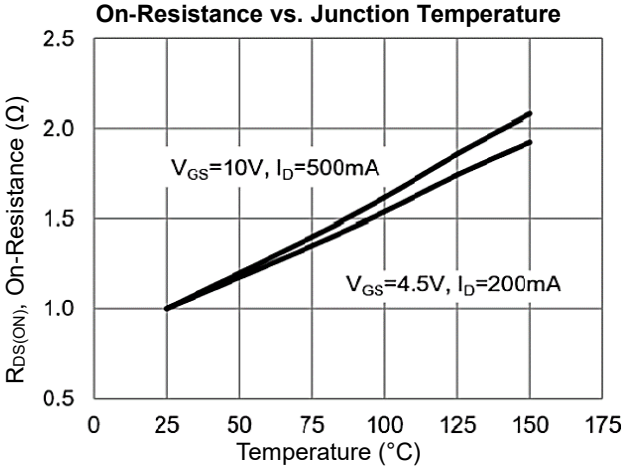
Transfer Characteristics



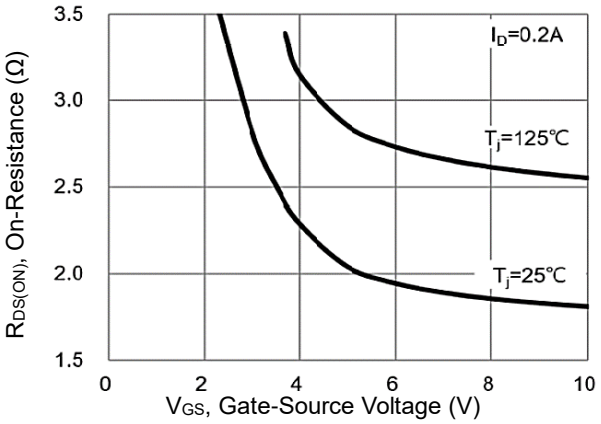
On-Resistance vs. Drain Current



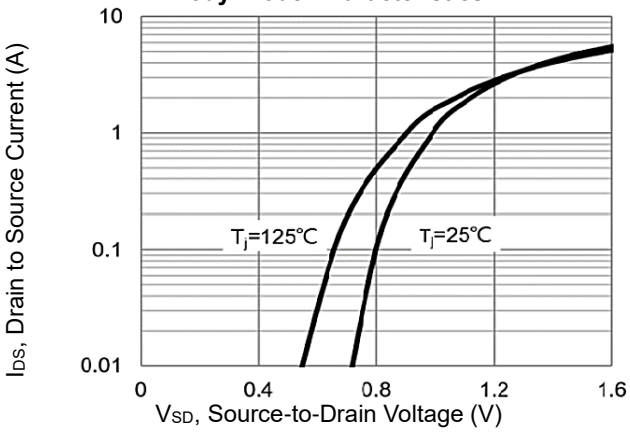
On-Resistance vs. Junction Temperature



On-Resistance Variation with V_{GS}

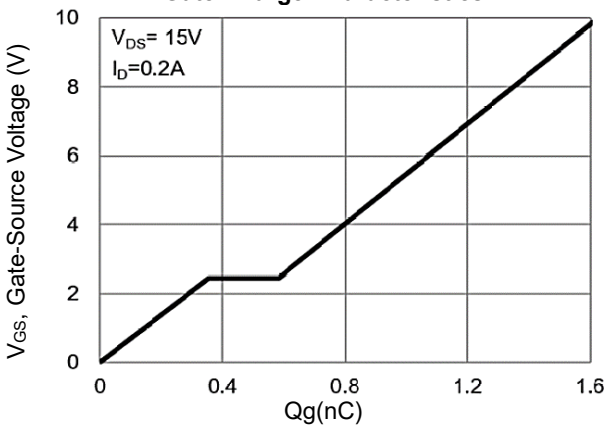


Body Diode Characteristics

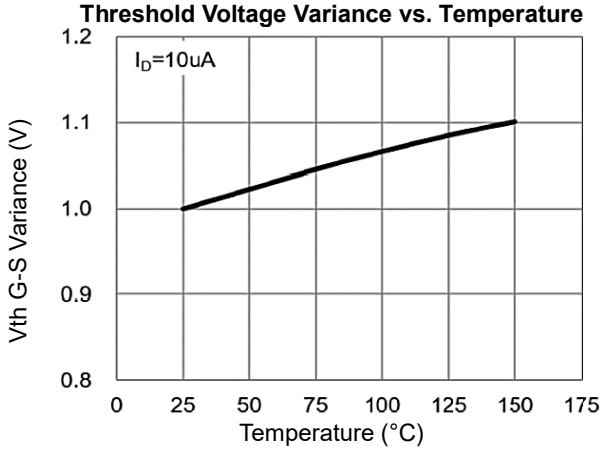


CHARACTERISTIC CURVES

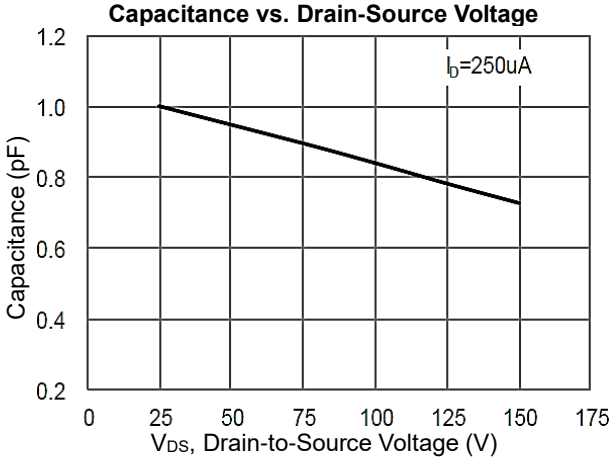
Gate Charge Characteristics



Threshold Voltage Variance vs. Temperature



Capacitance vs. Drain-Source Voltage



Breakdown Voltage vs Junction Temperature